NSN 5962-01-365-2256

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Maximum Power Dissipation Rating:
633.0 milliwatts
Operating Tempurature Range:
55.0/+125.0 degrees celsius
Storage Tempurature Range:
65.0/+150.0 degrees celsius
End Application:
_ug in unit e/i fscm 76301
Features Provided:
Programmed
nclosure Material:
Ceramic
nclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Case Outline Source And Designator:
D-2 mil-m-38510
Ferminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital-programmable read only memory (prom)
Voltage Rating And Type Per Characteristic:
0.5 volts applied and 7.0 volts applied
Time Rating Per Chacteristic:
50.00 nanoseconds af output megawatts
Memory Device Type:
Prom
Hybrid Technology Type:
Monolithic
Test Data Document:
76301-75b049008-1003 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer
drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Ferminal Type And Quantity:
16 printed circuit
Specification Data:
96906-mil-std-883 government standard
Shelf Life:
N/a
Unit Of Measure:

Yes - demil/mli

Demilitarization:

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